

# 2CL80KV/0.5A

## 0.5A 80kV--High voltage silicon rectifier stack

HVGT high voltage bridge rectifier is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

### **FEATURES:**

- 1. High reliability design.
- 2. High voltage design.
- 3. Power frequency ratio.
- 4. Conform to RoHS.
- 5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

### **APPLICATIONS:**

- 1. Ignition device power supply.
- 2. Microwave emission power.
- 3. General purpose high voltage rectifier.

### **MECHANICAL DATA:**

- 1. Case: epoxy resin molding.
- 2. Terminal: built-in M3 nut.
- 3. Net weight: 90grams (approx).

# HVGT Name: HVC-103020 XXXXXXXXX HVGT HVGT

(Unit: mm)

**MAXIMUM RATINGS AND CHARACTERISTICS:** (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	Vrrm	Ta=25°C;	80.0	kV
Average Output Current	Io	Ta=25°C;Resistive Load	0.5	A
Suege Current	Ifsм	Ta=25°C;8.3 mS	15.0	A
Junction Temperature	TJ		-40~+125	°C
Allowable Operation Case Temperature	Тс		125	°C
Storage Temperature	Тѕтс		-40~+125	°C

### **ELECTRICAL CHARACTERISTICS:** Ta=25°C (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V <sub>F</sub>	at 25°C;I <sub>F</sub> =I <sub>F(AV)</sub>	96	V
Maximum Reverse Current	Ir1	at 25°C;V <sub>R</sub> =V <sub>RRM</sub>	5.0	uA
	Ir2	at 100°C;V <sub>R</sub> =V <sub>RRM</sub>	50.0	uA
Maximum Reverse Recovery Time	Trr	at 25°C; I <sub>F</sub> =mA; I <sub>R</sub> =mA; I <sub>RR</sub> =mA		nS
Junction Capacitance	Сл	at 25°C; V <sub>R</sub> =0V; f=1MHz		pF